

DUAL DOUBLE GATE TRANSISTOR AND METHOD FOR FORMING

ABSTRACT OF THE DISCLOSURE

The present invention provides a dual gate transistor and a method for forming the same that results in improved device performance and density. The present invention uses a double gate design to implement a dual gate transistor. A double gate is a gate which is formed on both sides of the transistor body. The present invention thus provides a transistor with two double gates in series that provide improved current control over traditional dual gate designs. The preferred embodiment of the present invention uses a fin type body with dual double-gates. In a fin type structure, the double gates are formed on each side of a thin fin shaped body, with the body being disposed horizontally between the gates.